EVVOSEMI®
THINK CHANGE DO

ESD TVS MOS LDO Diode Sensor DC-DC

Product Specification

Domestic Part Number	IRLU120N
Overseas Part Number	IRLU120N
Equivalent Part Number	IRLU120N

N-Ch 100V Fast Switching MOSFETs

- ★ Advanced high cell density Trench technology
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Green Device Available

Product Summary

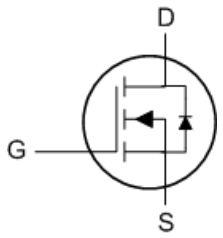
BVDSS	RDSON	ID
100V	152mΩ	9 A

Description

The IRLU120N is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The IRLU120 meet the RoHS and Green Product requirement with full function reliability approved.

TO251 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	9	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	5.7	A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	2.3	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	1.8	A
I_{DM}	Pulsed Drain Current[2]	18	A
P_D@T_A=25℃	Total Power Dissipation[3]	31	W
P_D@T_C=25℃	Total Power Dissipation[3]	2	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	4	℃/W

N-Ch 100V Fast Switching MOSFETs

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.122	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=8A	---	---	152	mΩ
		V_{GS}=4.5V , I_D=6A	---	---	158	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	---	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.84	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V , V_{GS}=0V , T_J=25℃	---	---	10	uA
		V_{DS}=80V , V_{GS}=0V , T_J=55℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=8A	---	10.2	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.3	---	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=60V , V_{GS}=10V , I_D=8A	---	25.5	---	nC
Q_{gs}	Gate-Source Charge		---	4.2	---	
Q_{gd}	Gate-Drain Charge		---	4.3	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=50V , V_{GS}=10V , R_G=3.3Ω I_D=1A	---	17.3	---	ns
T_r	Rise Time		---	2.8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	50	---	
T_f	Fall Time		---	2.8	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	1077	---	pF
C_{oss}	Output Capacitance		---	46	---	
C_{rss}	Reverse Transfer Capacitance		---	32	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	9	A
I_{SM}	Pulsed Source Current[2,4]		---	---	18	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The power dissipation is limited by 150℃ junction temperature
4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

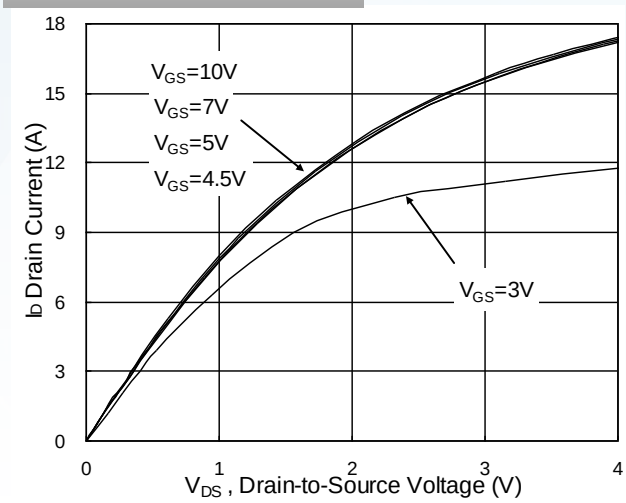


Fig.1 Typical Output Characteristics

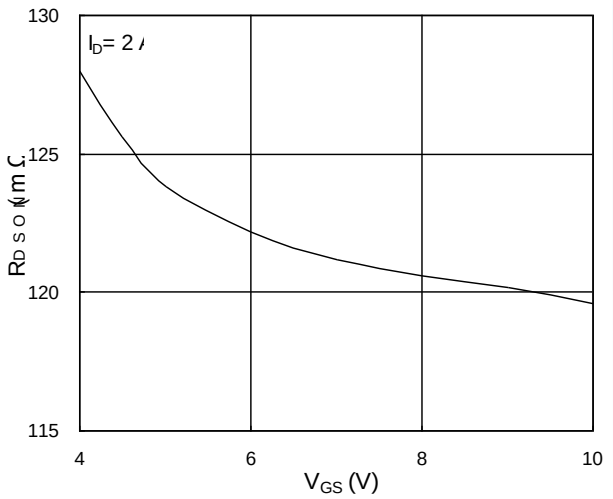


Fig.2 On-Resistance vs. Gate-Source

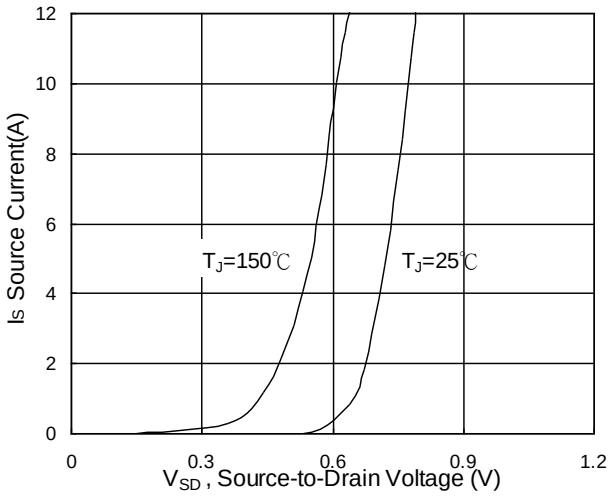


Fig.3 Forward Characteristics Of Reverse

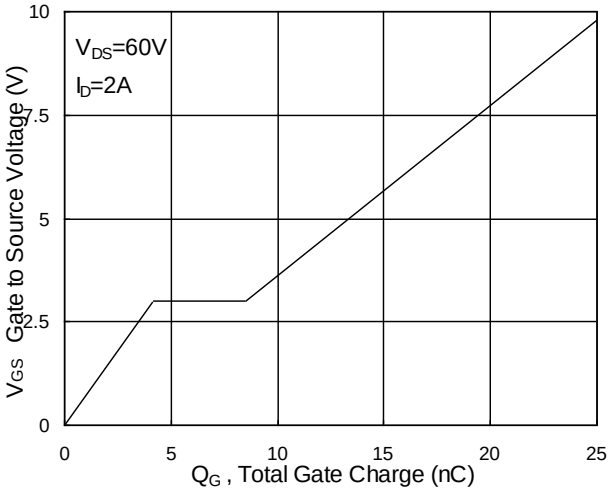


Fig.4 Gate-Charge Characteristics

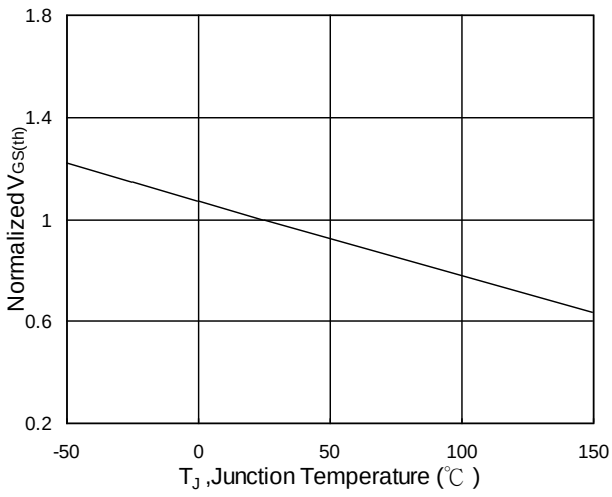


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

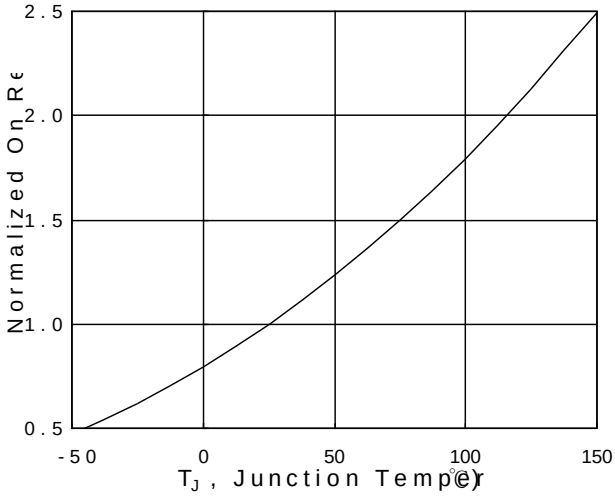


Fig.6 Normalized R_{DSON} vs. T_J

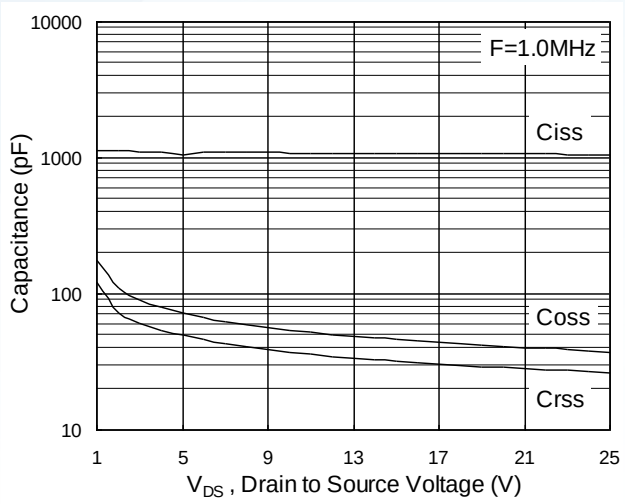


Fig.7 Capacitance

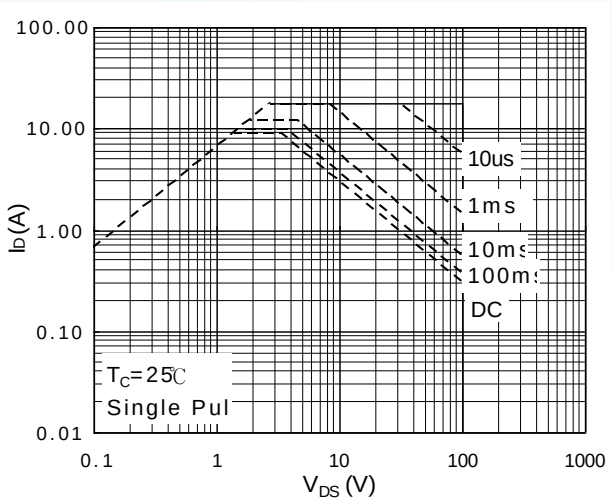


Fig.8 Safe Operating Area

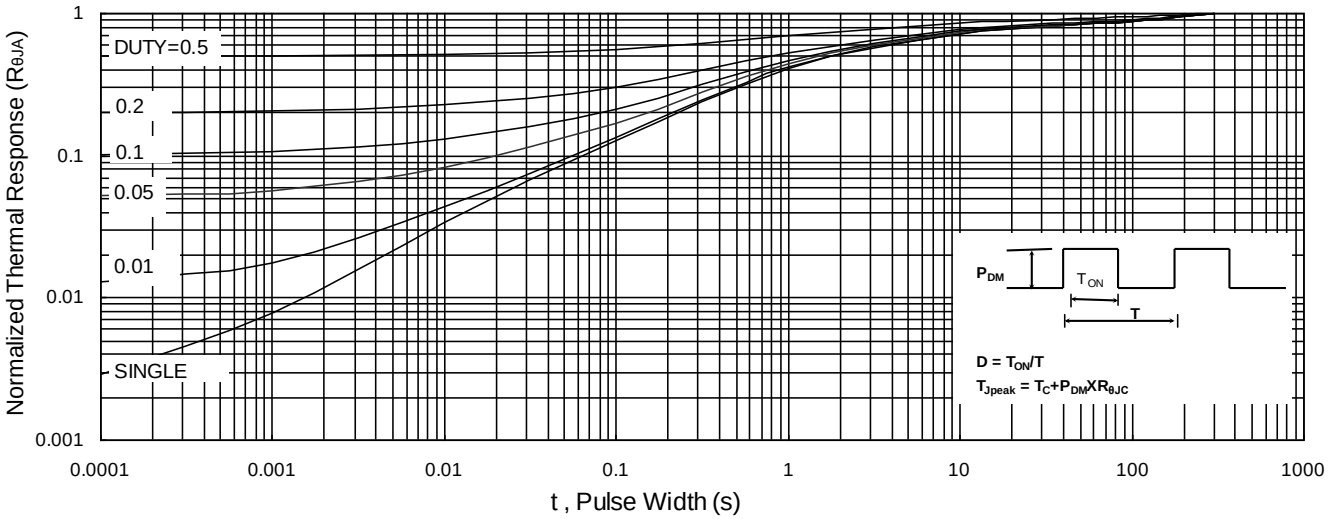


Fig.9 Normalized Maximum Transient Thermal Impedance

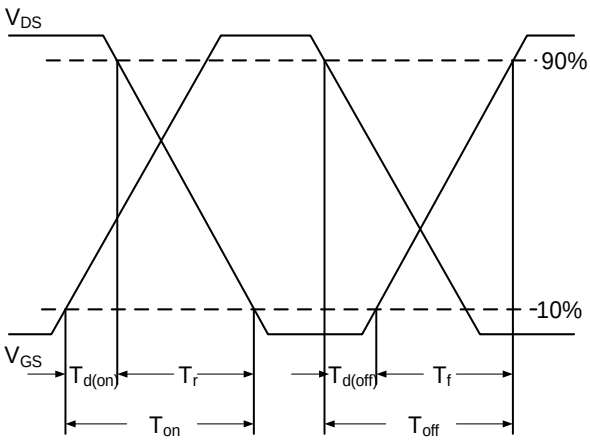


Fig.10 Switching Time Waveform

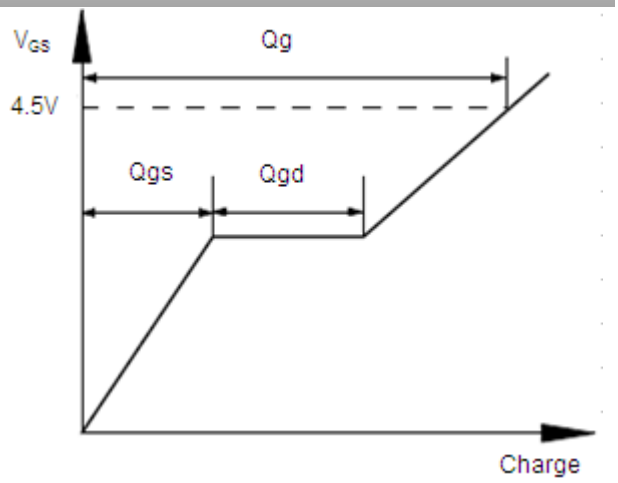


Fig.11 Gate Charge Waveform

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